Vishay Semiconductors

Ultrafast Soft Recovery Diode, 80 A FRED Pt®



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PowerTab[®]

LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS					
I _{F(AV)}	80 A				
V _R	400 V				
V _F at I _F	0.92 V				
t _{rr} (typ.)	See recovery table				
T _J max.	175 °C				
Package	PowerTab®				
Circuit configuration	Single				

FEATURES

- Ultrafast recovery time
- 175 °C max. operating junction temperature
- Screw mounting only
- Designed and qualified according to JEDEC®-JESD 47
- PowerTab[®] package
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

BENEFITS

- Reduced RFI and EMI
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION / APPLICATIONS

These diodes are optimized to reduce losses and EMI/RFI in high frequency power conditioning systems. The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for HF welding, power converters and other applications where switching losses are not significant portion of the total losses.

MECHANICAL DATA

Case: PowerTab®

Molding compound meets UL 94 V-0 flammability rating **Terminal:** nickel plated, screwable

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS	
Cathode to anode voltage	V _R		400	V	
Continuous forward current	I _{F(AV)}	T _C = 101 °C	80		
Single pulse forward current	I _{FSM}	T _C = 25 °C	800	А	
Maximum repetitive forward current	I _{FRM}	Square wave, 20 kHz	160		
Operating junction and storage temperatures	T _J , T _{Stg}		-55 to +175	°C	

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V_{BR}, V_{R}	I _R = 100 μA	400	-	-	
		I _F = 80 A	-	1.1	1.3	v
Forward voltage V _F	V _F	I _F = 80 A, T _J = 175 °C	-	0.92	1.08	v
		I _F = 80 A, T _J = 125 °C		0.98	1.15	
	$V_{R} = V_{R}$ rated	-	-	50	μA	
Reverse leakage current	I _R	$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	-	2	mA
Junction capacitance	CT	V _R = 200 V	-	50	-	pF
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	3.5	-	nH

Revision: 20-Nov-2023

Document Number: 97206

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COMPLIANT

HALOGEN



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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 $^{\circ}$ C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
		$I_F = 1 \text{ A}, \ dI_F/dt = 200 \text{ A}$	/dt = 200 A/μs, V _R = 30 V		50	60	
Reverse recovery time	t _{rr}	T _J = 25 °C		-	87	-	ns
		T _J = 125 °C		-	151	-	
Peak recovery current	I _{RRM}	T _J = 25 °C	I _F = 80 A V _R = 200 V dI _F /dt = 200 A/μs	-	9.3	-	А
Feak recovery current		T _J = 125 °C		-	17.2	-	~
	0	T _J = 25 °C		-	405	-	nC
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	1300	-	ne

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Thermal resistance, junction to case	R _{thJC}		-	-	0.70	°C/W
Thermal resistance, junction to heatsink	R _{thCS}	Mounting surface, flat, smooth, and greased	-	0.2	-	0/10
Weight			-	-	5.02	g
Mounting torque			1.2		2.4	N·m
Mounting torque			(10)	-	(20)	$(lbf \cdot in)$
Marking device		Case style PowerTab [®]	80EBU04			

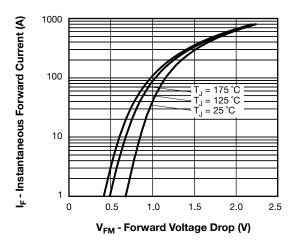


Fig. 1 - Maximum Forward Voltage Drop Characteristics

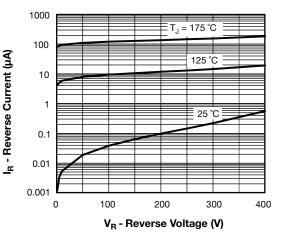
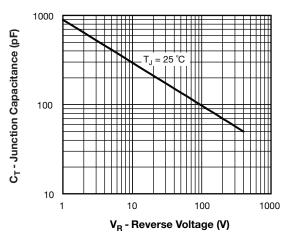
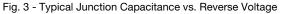


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage





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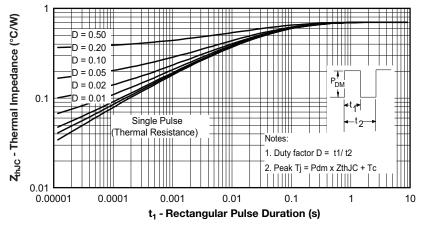
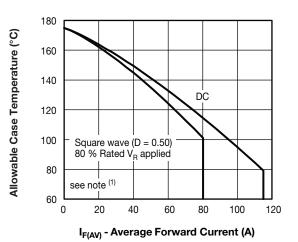
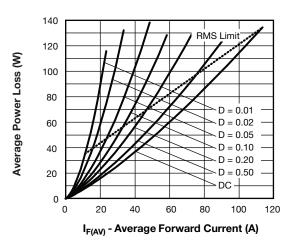


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics



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Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current





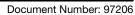
Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

 $\begin{array}{l} Pd = \mbox{forward power loss} = I_{F(AV)} \times V_{FM} \mbox{ at } (I_{F(AV)}/D) \mbox{ (see fig. 6);} \\ Pd_{REV} = \mbox{inverse power loss} = V_{R1} \times I_R \mbox{ (1 - D); } I_R \mbox{ at } V_{R1} = 80 \ \% \ \mbox{rated } V_R \end{array}$

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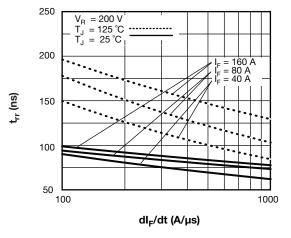


Fig. 7 - Typical Reverse Recovery Time vs. dI_{F}/dt

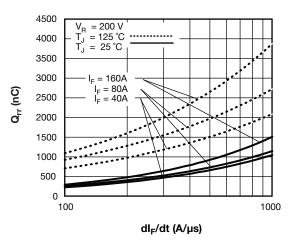


Fig. 8 - Typical Stored Charge vs. dl_F/dt



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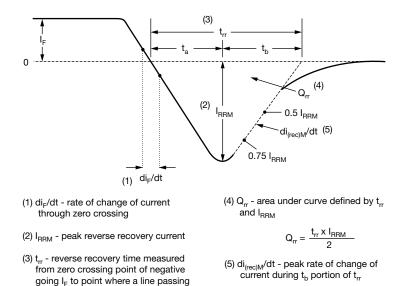
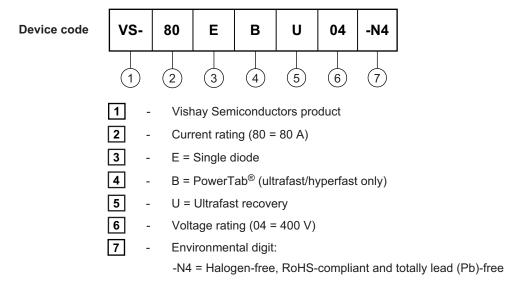


Fig. 9 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

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through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.

ORDERING INFORMATION (Example)				
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION		
VS-80EBU04-N4	25/tube	Antistatic plastic tube		

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95240			
Part marking information	www.vishay.com/doc?95467			
Application note	www.vishay.com/doc?95179			

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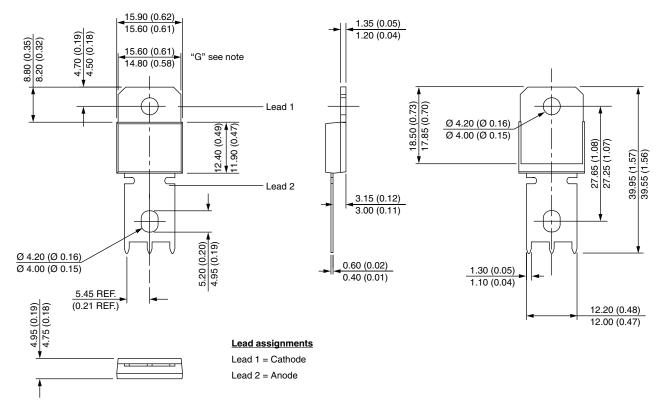
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DIMENSIONS in millimeters (inches)



Note:

Outline conform to JEDEC® TO-275, except for dimension "G" only



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Revision: 01-Jul-2024